rm PTO-1449  WAY 2 1 1999 U.S. Department of Commerce Page 8-83)  WAY 2 1 1999 U.S. Department of Commerce Page 8-83)		Attorney Docket No. 0756-1641		Serial No. 08/811,742		
<u>u</u>			Applicant: Hongyong ZHANG et al.			
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